Amendments to the Specification

Please replace the paragraph beginning at page 4, line 24 with the following amended paragraph:

In order to remove fine particles present in a discharge space, there is a method of causing a material gas flow in a direction parallel to a substrate on which a film is to be formed, as disclosed in Japanese Examined Patent Application Laid-Open No. Sho 62-43554. Fig. 3 shows a material gas flow in the case where a material gas is flowed in a direction parallel to a substrate on which a film is to be formed. In this method, a gas flow parallel to a substrate 301 on which a film is to be formed (hereinafter, referred to simply as substrate 301) gradually contains a flow 306 toward the substrate 301 due to turbulence of the gas flow while moving over a long distance between the substrate 301 and a discharge electrode 303. Fine particles generated in a discharge space 304 or fragmental particles generated by exfoliation of the film deposited on the discharge electrode 303 move along the gas flow. A part of the particles flow in the direction of the substrate 301 due to turbulence or diffusion of the gas flow to adhere onto the substrate 301. Moreover, as disclosed in Japanese Patent Application Laid-Open No. Hei 5-144595, there is also a method of introducing a gas flow from one direction of an enclosed space containing a discharge electrode and exhausting the gas flow from another direction. Also in this method, since fragmental particles and fine particles move along the gas flow over a long distance between a substrate and a film formation surface opposing thereto, a part of the particles flow in the direction of the substrate on which a film is to be formed due to turbulence or diffusion of the gas flow to adhere thereto.